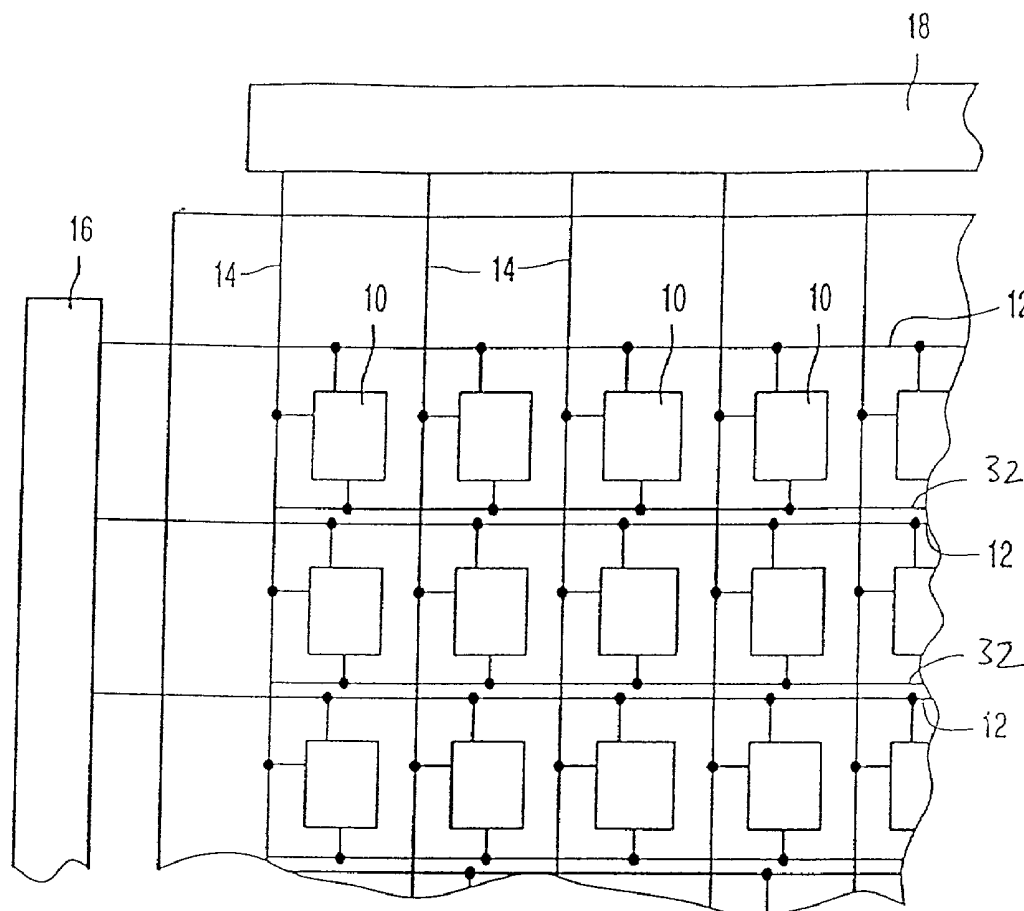




(43) **Pub. Date:** **Dec. 20, 2001**



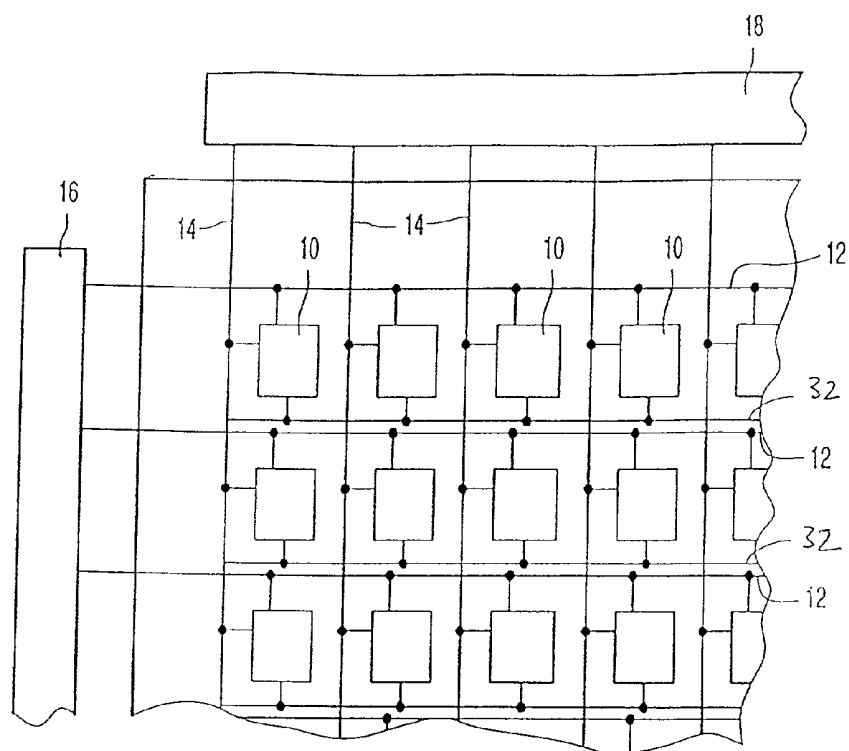
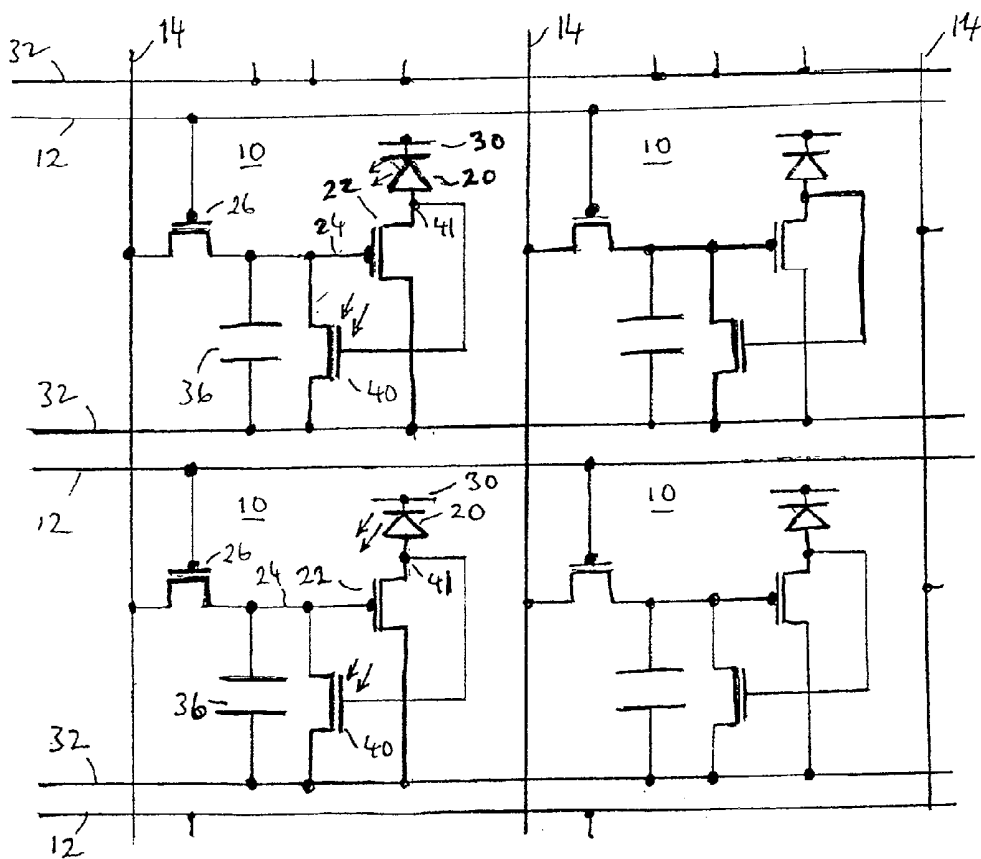


FIG. 1



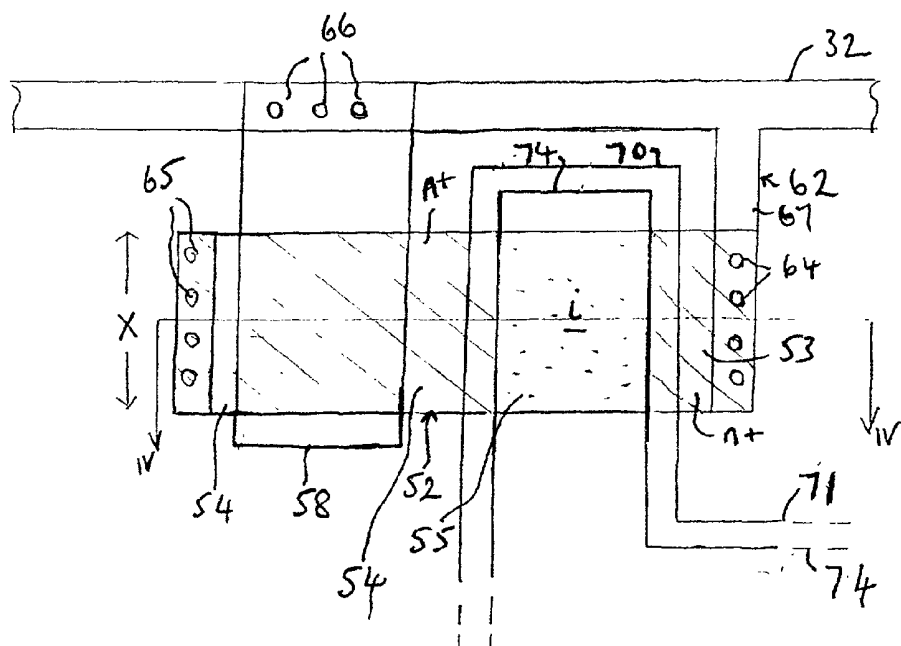


Fig. 3.

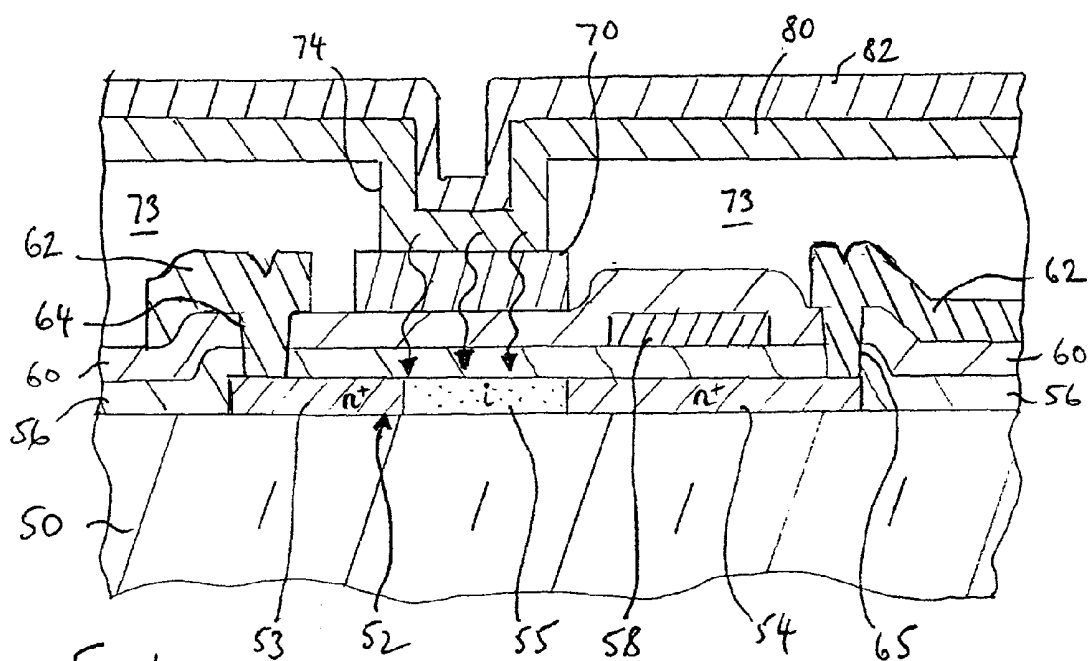


Fig. 4.

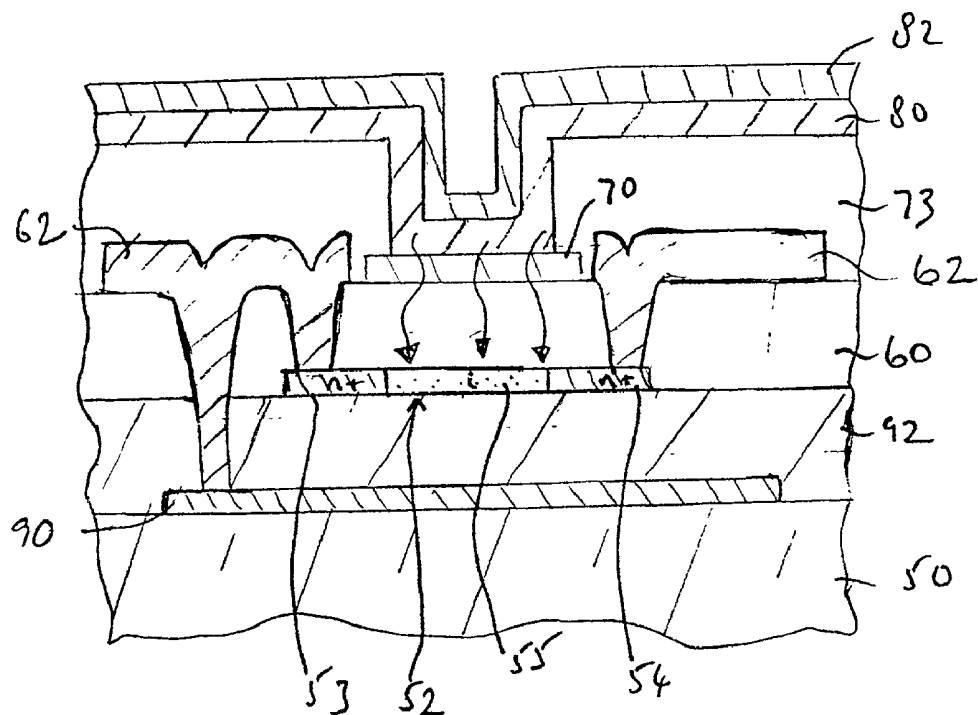


Fig. 5.

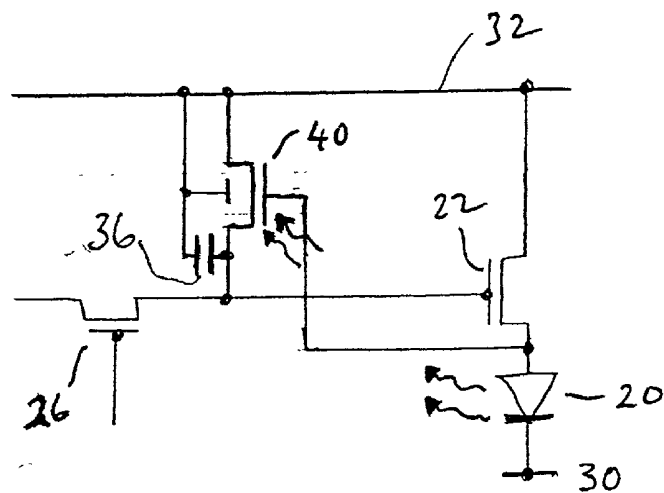


Fig. 6.

LIGHT-EMITTING MATRIX ARRAY DISPLAY DEVICES WITH LIGHT SENSING ELEMENTS

[0001] This invention relates to light emitting matrix array display devices with light sensing elements. More particularly, the invention is concerned with a matrix array display device comprising an array of addressable pixels comprising light-emitting display elements, and light sensing elements. The invention is concerned especially, but not exclusively, with matrix display devices using electroluminescent display elements, particularly organic electroluminescent display elements, OLEDs, including polymer electroluminescent elements, PLEDs.

[0002] An example of matrix display device whose pixels comprise electroluminescent (EL) display elements and light sensing elements is described in British Application No 0005811.5. The described device comprises an active matrix display device having an array of pixels carried on a substrate, in which each pixel includes a current-driven electroluminescent display element comprising light emitting EL material between two electrodes, one of which is transparent, and a switching device operable to control the current through the display element, and hence its light output, in a drive period based on a drive (data) signal applied to the pixel in a preceding address period.

[0003] As in other active matrix EL display devices, such as the device described in EP-A-0717446, the display elements, which need to continuously pass current in order to generate a light output, can be energised for an extended period, up to a frame time, following the addressing of the pixel in a respective row address period with the level of the data signal stored in the pixel in the address period determining its output during this drive period. The driving device, in the form of a thin film transistor (TFT), is responsible for controlling the current through the display element and the applied data signal is stored as a charge on a capacitance coupled to the gate of this drive TFT so that the operation of the TFT is dependent on the stored charge.

[0004] The pixels in the device of British Patent Application No 0005811.5 further include a thin film photosensitive device, comprising a (PIN) photodiode or a photo-responsive TFT coupled to the storage capacitance that is arranged in operation of the pixel to be reverse biased and is responsive to light emitted by the pixel's display element in the drive period so as to leak charge from the capacitance at a rate dependent on the display element's light output level. Thus, by virtue of the photo sensitive device, opto-electronic feedback is provided which progressively adjusts the operation of the drive TFT controlling energisation of the display element during the drive period to reduce the current flow through the display element, and hence its light output, by progressively discharging the capacitance (assuming it is charged upon addressing). The proportion of the total available drive period for which the display element is energised is, therefore, dependent on, and regulated by, this feedback arrangement according to the element's light output. In this way the integrated light output from a display element in a drive (frame) period can be controlled so as, inter alia, to counteract any effects of ageing or degradation in the display element's electroluminescent material, particularly a reduction in light output level for a given drive current level, which can occur over a period of time of operation, and also to compensate for the effects of voltage drops occurring in current carrying lines supplying the pixels.

[0005] Such a technique is valuable in achieving a high quality display by ensuring that pixel light outputs can be constant and uniform over time. However, the implementation of such a pixel circuit can be problematic. The photocurrent generated by the photosensitive device needs to be very small in order to appropriately control the TFT gate potential over a frame period if the use of a large storage capacitance is to be avoided. Also, the provision in each pixel circuit of the light sensitive element using thin film technology ideally should not unduly complicate fabrication while at the same time good optical coupling between the light-emitting display element and the light sensing element needs to be ensured.

[0006] According to the present invention, there is provided a light emitting display device comprising on a substrate an array of addressable pixels each comprising a light-emitting display element having a layer of light-emitting material with a transparent electrode on one side thereof, and a light sensing element responsive to light emitted by the display element, wherein each light sensing element comprises a gated photosensitive thin film device comprising a semiconductor layer having contact regions laterally spaced on the substrate and an intervening gate controlled region over which dielectric material is disposed, and wherein a part of the light-emitting display element extends over the dielectric material and the gate controlled region such that the transparent electrode of the light-emitting display element at that part serves as the gate of the photosensitive device and light emitted by the light-emitting material layer is incident on the semiconductor layer.

[0007] With this arrangement, the provision of the light sensing element is relatively uncomplicated while at the same time good optical coupling between this component and the light-emitting material of the display element is reliably ensured. Such an arrangement, therefore, is highly beneficial when used, for example, in the kind of display device described in the aforementioned application No 0005811.5. The basic structure of the gated photosensitive device is generally similar to that of TFTs commonly used in matrix display devices, e.g. the driving TFTs of the aforementioned display device. In this respect, the gated photosensitive device may comprise a TFT or a gated lateral (pin) diode. The provision of this component is, therefore, entirely compatible with the thin film technology used for matrix display devices and the device can easily be formed simultaneously with such TFTs from common thin film layers. Because a part of the light-emitting element extends over the photo device and the active region of the device is directly and closely associated with the light-emitting material, then the device is highly responsive to variations in light output from the light-emitting material. Moreover, as a part of the electrode of the light-emitting element is utilised for the gate of the photosensitive device, then the gate potential of this device, corresponding to the potential of this electrode in operation of the device, can conveniently be biased appropriately during operation such that it behaves as a photosensitive leakage device by virtue of photocurrents generated therein in response to light incident from the light-emitting layer in the manner required for this component when used as a charge adjusting device in the display device of the aforementioned type.

[0008] While the invention is particularly beneficial in the implementation of the particular kind of pixel circuit dis-

cussed above, it is envisaged that it can be used to advantage in other light emitting matrix display devices in which pixels include a light sensing device responsive to the light emission of the pixel's display element for another purpose rather than being used in the particular manner described.

[0009] The light-emitting elements preferably comprise electroluminescent elements, such as OLED or PLED elements. However, it is envisaged that the invention could be used to similar advantage in display devices using other kinds of light-emitting elements and not necessarily in the case of the light sensing element being used as part of an electro-optic feedback arrangement in the manner described.

[0010] Embodiments of light-emitting display devices in accordance with the invention, and in particular active matrix EL display devices, will now be described, by way of example, with reference to the accompanying drawings in which:

[0011] **FIG. 1** is a simplified schematic diagram of an embodiment of an active matrix EL display device according to the present invention;

[0012] **FIG. 2** shows the equivalent circuit of a few typical pixels in the device of **FIG. 1**;

[0013] **FIGS. 3 and 4** are respectively plan and sectional schematic views of part of a pixel;

[0014] **FIG. 5** is a schematic view through a part of an alternative form of pixel in a further embodiment; and

[0015] **FIG. 6** shows the equivalent circuit of a typical pixel in the further embodiment.

[0016] The Figures are merely schematic. The same reference numbers are used throughout the Figures to denote the same or similar parts.

[0017] Referring to **FIG. 1**, the active matrix electroluminescent display device comprises a panel having a row and column matrix array of regularly-spaced pixels, denoted by the blocks **10**, each comprising an electroluminescent display element and an associated driving device controlling the current through the display element, and which are located at the intersections between crossing sets of row (selection) and column (data) address conductors, or lines, **12** and **14**. Only a few pixels are shown here for simplicity. The pixels **10** are addressed via the sets of address conductors by a peripheral drive circuit comprising a row, scanning, driver circuit **16** and a column, data, driver circuit **18** connected to the ends of the respective conductor sets.

[0018] Each row of pixels is addressed in turn in a frame period by means of a selection signal applied by the circuit **16** to the relevant row conductor **12** so as to load the pixels of the row with respective data signals, determining their individual display outputs in a frame period following the address period, according to the respective data signals supplied in parallel by the circuit **18** to the column conductors. As each row is addressed, the data signals are supplied by the circuit **18** in appropriate synchronisation.

[0019] **FIG. 2** illustrates the circuit of a few, typical, pixels. Each pixel **10** includes a light emitting organic electroluminescent display element **20**, represented here as a diode element (LED), and comprising a pair of electrodes between which one or more active layers of organic electroluminescent light-emitting material is sandwiched. In this

particular embodiment the material comprises a polymer LED material, although other organic electroluminescent materials, such as low molecular weight materials, could be used. The display elements of the array are carried, together with the associated active matrix circuitry, on the surface of an insulating substrate. The substrate is of transparent material, for example glass, and the electrodes of the individual display elements **20** closest to the substrate consist of a transparent conductive material such as ITO so that light generated by the electroluminescent layer is transmitted through these electrodes and the substrate so as to be visible to a viewer at the other side of the substrate. The cathodes of the display elements comprise a metal having a low work-function such as calcium, a magnesium silver alloy, or a barium/aluminium dual layer. Examples of suitable organic conjugated polymer materials which can be used are described in WO 96/36959. Examples of other, low molecular weight, organic materials are described in EP-A-0717446, which also describes the construction and operation of a typical known form of active matrix electroluminescent device and whose disclosure in these respects is incorporated herein by reference.

[0020] Each pixel **10** includes a driving device in the form of a low temperature polysilicon TFT **22**, here of p-type conductivity, which is responsible for controlling the current through, and hence operation of, the display element **20** on the basis of a data signal voltage applied to the pixel. A data signal voltage for a pixel is supplied via a column conductor **14** which is shared between a respective column of pixels. The column conductor **14** is coupled to the gate of the current-controlling drive TFT **22** through an address TFT **26**, also of p-type. The gates for the address TFTs **26** of a row of pixels are all connected to a common row conductor **12**.

[0021] Each row of pixels **10** also shares a common voltage supply line **30** held at a predetermined potential, and normally provided as a continuous electrode common to all pixels, and a respective common current line **32**. The display element **20** and the driving TFT **22** are connected in series between the voltage supply line **30** and the common current line **32** which acts as a current source for the current flowing through the display element **20**. The line **30**, for example, may be at ground potential and the line **32** at a positive potential around, for example, 12V with respect to the supply line **30**. The current through the display element **20** is regulated by the drive TFT **22** and is a function of the gate voltage on the TFT **22**, which is dependent upon a stored control value determined by the data signal.

[0022] An individual row of pixels is selected and addressed by the row driver circuit **16** applying a selection pulse to its associated row conductor **12** which turns on the address TFTs **26** of the pixels and defines a respective row address period. A data signal, in the form of a voltage level derived from the video information supplied to the driver circuit **18** and applied to the column conductor **14** by the driver circuit **18**, is transferred by the address TFT **26** to the gate node **24** of the drive TFT **22**. At the end of the row address period the address transistor **26** turns off, and the voltage on the gate node **24** is retained by a pixel storage capacitor **36** connected between the gate of the TFT **22** and the common current line **32**, so as to maintain the operation of the display element during the subsequent drive period.

[0023] The voltage between the gate of the TFT **22** and the common current line **32** determines the current passing

through the display element **20**, the current flowing through the display element being a function of the gate-source voltage of the drive TFT **22** (the source of the p-channel type TFT **22** being connected to the common current line **32**, and the drain of the TFT **22** being connected to the display element **20**). This current in turn controls the light output level (grey-scale) of the pixel. The TFT **22** is biased as a current source and operates in saturation, so that the current flowing through the TFT is insensitive to the drain-source voltage and dependent on the gate-source voltage. Consequently, slight variations of the drain voltage do not affect the current flowing through the display element **20**. The voltage on the voltage supply line **30** is therefore not critical to the correct operation of the pixels.

[0024] Each row of pixels is addressed in turn in this manner in a respective row address panel so as to load the pixels of each row in sequence with their respective drive signals and set the pixels to provide desired display outputs during the subsequent drive period, corresponding approximately to a frame period, until they are next addressed.

[0025] In each pixel an opto-electronic arrangement is employed to compensate for effects of display element degradation, whereby the efficiency of its operation in terms of the light output level produced for a given drive current diminishes. Through such degradation display elements that have been driven longer and harder will exhibit reduced brightness, causing display non-uniformities. The opto-electronic arrangement counteracts these effects to an extent by controlling the integrated, total, light output from an element in a drive period accordingly. The pixel circuits are similar in this respect to those described in British Patent Application No. 0005811.5 to which reference is invited for a fuller description of such operation and whose disclosure in this respect is incorporated herein by reference. Briefly, electro-optical feedback is used to adjust the charge on the storage capacitor during the drive period by discharging the capacitor at a rate dependent on the instantaneous light emission of the display element during this period. Consequently, for a given data signal value the length of time for which a display element is energised to generate light during the drive period following the address period is regulated according to the subsisting drive current/light emission level characteristic of the display element, as well as the level of the applied data signal, such that the effects of degradation, particularly with regard to display non-uniformities, are reduced and the light output from individual pixels can then be substantially the same as would be obtained with a non-degraded display element if required.

[0026] Referring to **FIG. 2** the electro-optic discharging means in this device comprises a gated photo-sensitive thin film device **40**, which here is in the form of another TFT whose current-carrying, source and drain, electrodes are connected across the storage capacitor **36**, to the gate node **24** of the drive transistor **22** and the current line **32**, and whose gate is connected to the node, **41**, between the drive TFT **22** and the display element **20**. In this particular embodiment, where the drive TFT **22** (and address TFT **26**) comprises an p-type low temperature polysilicon MOS TFT, then the device **40** is of an opposite conductivity type, i.e. a n-type polysilicon MOS TFT.

[0027] As will be described in greater detail, the pixel is constructed and arranged in such a way that the gated

photo-sensitive device **40** is exposed to light emitted by the display element **20** in operation of the pixel. At the end of the addressing phase a voltage is set on the gate node **24** of the drive TFT **22**, according to the level of the applied data signal, and the capacitor **36**, charged to this voltage level, serves to maintain the gate voltage of the TFT **22**, at least initially, in the subsequent drive phase. The drain junction of the photosensitive device **40** coupled to the line **32** is reverse biased and photo-responsive, and light emitted by the display element in the drive period causes a small photocurrent to be produced in the device **40** which is approximately linearly proportional to the display element's instantaneous light output level. The effect of this photocurrent is to slowly discharge the storage capacitor **36**, the amount of photocurrent, and thus the rate of discharge, being dependent on the light output level of the display element. The gate of the TFT **40** is positively biased, with its voltage corresponding to the voltage at the node **41** and always zero or negative with respect to the node **24**, and always negative with respect to the line **32**, and this ensures that the TFT **40** is held in its off (non conductive) state. Accordingly, the transistor **40** behaves merely as a leakage device, in the manner of a reverse biased photodiode, which causes leakage of charge on the capacitor **36**. The resultant discharging of the capacitor **36** in the drive period leads to the voltage on the gate of the drive TFT **22** gradually reducing which in turn progressively lowers the current flowing through the display element **20** with the light output of the display element gradually decreasing in corresponding fashion, until the TFT **22** approaches its threshold, turn-off, level. The reduction in current flowing through the display element **20** leads to a gradual increase in the (positive) voltage level at the node **41**, although this merely ensures that the TFT **40** is continuously held off. When, eventually, the voltage on the gate node **24** drops to below the TFT's threshold voltage, the light output is terminated. As examples of typical voltages present in operation of the pixel, assuming for example that the TFT **22** has a -5 volt threshold, the voltage supply line **30** may be at around 0 volts, the common current line **32** may be at 12 volts, and as the voltage at the gate node of the transistor **22** changes from 4 to 12 volts the voltage at the node **41** can change from 4 volts to 0 volts.

[0028] By regulating the total, integrated, amount of light emitted by the display element within the drive period, which a viewer perceives as brightness, the effects of display element degradation can be counteracted. The integrated light output (brightness) is dependent on the length of time in the drive period for which the display element is energised as well as its initial light level. Because of the action of the discharging means in controlling the duration for which the display element is energised in the drive period, then different pixels in the array supplied with the same data signal value will tend to produce similar perceived brightness levels regardless of variations in the characteristics of their individual display elements due to degradation. In other words, the integral of the light outputs from individual display elements addressed with the same data signal value will be similar even though at the start of the drive period their respective light output levels may differ due to degradation effects. Improved uniformity of display output is thus obtainable.

[0029] As usual, the level of the applied data signal is adjusted appropriately to provide different grey-scale levels from the pixels. If the data signal, and thus charge on the

gate node **24**, is increased then more photons are required from the display element during the drive period before the TFT **22** is caused to switch off, so that a higher grey-scale level is achieved, and vice versa.

[0030] This manner of operation is effective also to compensate automatically for variations in the operational characteristics of the TFTs **22** of different pixels in the array resulting, for example, from variations in their threshold voltages, dimensions, and mobilities due to the nature of the thin film fabrication processes used to form the TFTs. Thus, further improvement in the uniformity of light output from the display elements over the array is achieved.

[0031] Referring now to FIGS. 3 and 4, there are shown schematic plan and sectional views through a part of a typical pixel including the photosensitive TFT **40** and illustrating the manner of the pixel construction at this region. FIG. 4 corresponds approximately to a sectional view along the lines IV-IV of FIG. 3. In addition to the TFT **40**, the part shown includes a portion of the display element **20** and the storage capacitor **36**, but does not encompass the addressing and drive TFTs **26** and **22**. It will be appreciated though that these latter components are fabricated together with the components shown using the same processes and from common deposited layers.

[0032] On the transparent insulating substrate **50** a semiconductor island **52** of elongate strip form and comprising a layer of low temperature polysilicon material is provided. This is obtained by laser recrystallising a CVD deposited amorphous silicon layer and appropriately patterning this layer using a mask and photolithographic processing. The semiconductor strip is generally rectangular in shape, having substantially parallel major sides, and thus having substantially constant width along its length. The opposing end portions of this island are doped (n+) to constitute laterally-spaced drain and source contact electrode regions **53** and **54** respectively which are separated by a co-planar region of intrinsic semiconductor material **55** forming a gate controlled, channel, region of the TFT **40**. Corresponding, similarly-shaped, islands of polysilicon are formed at other intended pixel locations on the substrate at the same time and together with semiconductor islands for the addressing and drive TFTs **26** and **22**, although the regions of these latter TFTs constituting source and drain electrodes are oppositely doped (p+type) instead. An insulating layer **56**, for example of silicon dioxide or nitride, is deposited continuously over the substrate to cover these islands and serve as a gate dielectric layer.

[0033] A layer of metal, for example of aluminium, or an aluminium alloy, is deposited over the layer **56** and patterned to leave regions constituting the gates (not shown) of the TFTs **26** and **22** and a region **58** overlying the (drain) region **53** at each photosensitive TFT location. At the same time, required interconnection lines are formed from this metal layer. As is apparent from FIGS. 3 and 4, the region **58** is defined as a rectangular finger or strip extending substantially transversely of the semiconductor island **52**. At the region of their cross-over, therefore, both the island **52** and the finger **58** are parallel-sided and of substantially constant width. Together, the overlying portions of the metal finger **58** and the n+region **54** and the intervening portion of the dielectric layer **56** constitute the pixel's storage capacitance **36**, whose capacitance value is determined by the cross-over

area between the finger **58** and the island **52** and the thickness and dielectric constant of the layer **56**.

[0034] Another dielectric layer **60**, e.g. of silicon oxide nitride, is formed over this structure covering, inter alia, the defined regions **58** of the metal layer. A further metallisation layer is then deposited and patterned to leave regions **62** forming the current lines **32** and other required interconnections. Prior to depositing this layer, contact openings **64** and **65** are formed by etching through both the dielectric layers **56** and **60** over the source region **53** and the drain region **54** and contact openings **66** are formed through the layer **60** over an end portion of the region **58** so that, following deposition and patterning of this metal, interconnections are provided between the current line **32**, via an integral extension arm **67**, and the drain electrode **53**, between the source region **54** and the gate node **24** via a part of the metallisation **62** forming the current lines (through further contact openings which are not shown), and between the current line **32** and the metal finger **58**.

[0035] Transparent conductive material such as ITO is then deposited and patterned to leave regions constituting lower (anode) electrodes for the display elements which are appropriately shaped to define the desired shape of the display elements. A portion of this electrode forms an integral leg **70** which extends away from the main display element area **71** (only a small part of which is shown) and transversely over the semiconductor island **52** directly above the gate controlled region **55** and the drain junction.

[0036] A further, relatively thick and continuous, dielectric layer **73** e.g. of silicon nitride or an even thicker (1-2 μm) insulating polymer layer is deposited completely over the structure and openings **74** are formed in this layer above the patterned ITO regions both at the legs **70** and main display element areas.

[0037] The polymer light emitting material is then deposited, for example by spin coating, as a continuous layer **80** extending over the dielectric layer **73** and into the openings **74** formed therein so as to contact directly with the underlying ITO. Over this layer **80**, a continuous layer **82** of calcium, magnesium silver alloy or barium/aluminium is deposited to form a common electrode layer constituting the display element cathode electrodes and the supply lines **30**.

[0038] Each display element **20** consists of a respective region **71** of ITO together with overlying portions of the layers **80** and **82** and it will be appreciated that the integral ITO leg **70** together with the immediately overlying parts of the layers **80** and **82** form an integral extension of the display element which with the main display element region emits light upon a suitable potential difference being applied between the bottom and top electrodes.

[0039] The portion of the ITO leg **70** immediately overlying the gate controlled region **55** serves as the gate of the photosensitive TFT **40** with the underlying combined layers **56** and **60** providing the gate dielectric.

[0040] In operation of the pixel, light emitted by the layer **80** upon current being passed between the electrodes **71** and **82** is transmitted through the ITO lower electrode and the substrate **50** to produce a display output. The leg of the display element similarly produces light and this passes through the ITO extension **70** and the underlying, transparent, dielectric layers **56** and **60** so as to be incident on the

gate controlled region **55** of the photosensitive TFT **40**. The light falling on the drain junction particularly is responsible for photocurrent being generated. Thus, as a result of the display element leg extending over the region **55**, and the light emitting polymer material **80** being immediately above the gate of TFT **40** and directly emitting light into the TFT structure, good optical coupling between the display element and the photosensitive TFT **40** is ensured and achieved in simple and reliable manner.

[0041] Moreover, as the gate of the TFT **40** is constituted by a portion of the display element anode, then the gate is always at the required (negative) bias with respect to both source and drain to ensure that the TFT **40** is held off (i.e. in its high resistance, non-conducting, state) and that only leakage currents due to generated photocurrents flow between its source and drain electrodes.

[0042] The relationship between the photosensitive TFT **40** and the storage capacitance **36** in terms of the level of photocurrent generated in response to typical input light levels and the amounts of charge stored on the storage capacitor **36** needs to be closely controlled in order for the electro-optic feedback control to be implemented most effectively. The active area of the TFT **40** in this respect comprises the edge of a lateral (n+-i) drain junction and it is only this comparatively narrow area at the drain junction which contributes a photocurrent. The active area is basically equivalent to a photodiode and desirably should be very small in order to ensure the typical levels of photocurrent generated are sufficiently low to control the gate potential of the drive TFT **22** in the manner required over the drive (frame) period and avoid the need to use a larger storage capacitor. Because the storage capacitor **36** uses in its structure only the layer **56** as the capacitor dielectric then the area required for the capacitor structure to provide a given capacitance value is much smaller than would be the case if both the layers **56** and **60** were used.

[0043] When using thin film technology it can be difficult to form components with very precise dimensional values because of the nature of the processes employed to define the components, e.g. the masking and etching steps used in photolithographic patterning processes. It will be appreciated that in the above-described structure the storage capacitor **36** and the photosensitive TFT **40** both share the same critical layer, namely the semiconductor island **52** and are spatially close. Accordingly, any line width variations in this part due to manufacturing tolerances will be common to both. Because this critical geometry, i.e. the width of the strip-shape island **52** as indicated by X in FIG. 3, is constant for both the TFT **40** and the storage capacitor then any deviation in this physical dimension of this common part from the intended value will affect both the active area of the TFT and the capacitance value of the storage capacitor in a similar, corresponding fashion. More precisely, the active area of the TFT and the capacitance value scale together. Any variation in the width of the island **52** tending to increase the size, and hence capacitance, of the storage capacitor will result in the size of active area of the TFT also being increased, and vice versa, so that the balance between the electrical characteristics of these two components will be maintained. Thus, the desired, and predetermined, inter-relationship of these two components is ensured.

[0044] A gated lateral p-i-n diode may conveniently be used in place of the TFT **40**. The structure of such a device

would be generally similar to that shown in FIG. 3 except that the region **53** of the semiconductor island **52** would be doped oppositely to the region **54**, i.e. p+ type. In reverse bias, the p+ region **53** is more positive than the n+ region **54**. In this case, light incident across the whole device can generate photocurrent. The photo-active junction thus will extend to a greater distance across the device than is the case with the previous, TFT, structure.

[0045] In the above described pixel embodiment, the photosensitive TFT **40** is of opposite conductivity type to both the address TFT **26** and the drive TFT **22**, and by virtue of the manner in which the gate of the TFT **40** is biased it is ensured that the TFT **40** is held off and acts simply in the manner of a reverse-biased photodiode to leak charge on the capacitor **26** during the drive period.

[0046] However, in an alternative form of this pixel circuit, the TFT **40** may be of the same type as the drive TFT **22** and operable also as a switching device rather than solely a leakage device. In operation of this alternative circuit, then initially at least in the drive period the gate potential, corresponding to the display element lower electrode/node **41** potential, will be such as to ensure that the TFT behaves as a simple, reverse-biased, leakage device. As this discharging continues then the consequential reduction in current flowing through the display element will lead to a gradual increase in the (negative) voltage level at the node **41** (FIG. 2). When the current level attains a certain lower limit, the voltage at the node **41** relative to the line **32** will reach the threshold voltage of the TFT **40** causing it to turn on (conduct) abruptly and rapidly discharge the capacitor **26** so that the drive TFT **22** turns off and energisation of the display element is terminated. The switching operation of the TFT **40** in this manner has the advantage that the light output of the display element is determined in a more precisely controller manner. Without such switching, the turning off of the display element could be less well controlled due to the fact that the behaviour of the photosensitive TFT **22** in response to comparatively low light input levels, as would occur towards the end of the display element's energisation phase, becomes less well defined and less predictable.

[0047] The photosensitive TFT **40** desirably is shielded from the effects of ambient light falling thereon so that any photocurrent is due solely to light emitted from the display element. To this end, the metal electrode layer **82** serves to shield the device from ambient light at one side of the panel. Shielding of light from the other side, through the transparent substrate **50**, could be achieved by depositing a light shield layer between the semiconductor island **52** and the substrate surface.

[0048] Preferably, however, in another embodiment of device according to the invention, the structure of the pixel is modified so that a part of the storage capacitor structure is employed also to act as a light shield. FIG. 5 illustrates schematically a section through a part of the modified pixel structure for comparison with FIG. 4. In this structure, a metal layer is deposited on the surface of the substrate **50** and patterned to form at each pixel a light shield **90** whose overall dimensions are slightly greater than those of the subsequently formed semiconductor island **52** used for the TFT **40** (or alternatively a lateral pin diode). An insulating layer **92**, for example of silicon nitride, is deposited as a

continuous layer completely over the substrate surface and those metal layers 90 to form a planar surface upon which the pixel structure is then fabricated generally as previously described but in this case with the metal finger 58 previously used being omitted and with the portion of the metal layer 62 used to contact the region 53 of the semiconductor island 52 being arranged also to contact one end of the light shield layer 90 through the dielectric layers 60 and 92 via a contact hole formed in these layers away from the island 52. The dielectric layer 56 is not necessary in this version.

[0049] In this construction, the storage capacitor 36 is formed by the part of the light shield layer 90 overlying contact region 54 of the island 52 together with the portion of the insulating layer 92 sandwiched therebetween which provides the dielectric. The equivalent circuit of this pixel is shown in FIG. 6. The photosensitive TFT 40 in this case effectively has a double gate, with the light shield 90 constituting a bottom gate. This second gate will be positive with respect to the channel 55 and so the insulating layer 92 is required to be sufficiently thick to ensure that the TFT's threshold level is not reached and that the TFT is prevented from being turned on.

[0050] Instead of overlying the island 52 completely as in the above arrangement, the layer 90 may be configured such that it adequately covers the photo-active region 53 of the TFT 40 for light shielding purposes by extending completely over the region of the drain junction and over the source region 54 to form the capacitor but does not extend to any significant extent over the channel region. To this end, the layer 90 may have a central aperture overlying the channel region 55 bounded and by integral arms extending parallel to the island to either side of the channel region so that the regions of the layer 90 overlying the two contact regions are interconnected. With this arrangement, then because the layer does not extend directly over the channel region 55 the risk of it acting as a second gate is avoided.

[0051] In this other embodiment, then again the TFT 40 and storage capacitor 36 both share the same critical layer, i.e. the island 52, so that any spatial variation due to fabrication process tolerances are common to both components and they scale together.

[0052] The invention can be used also with pixels driven using a current data signal rather than a voltage data signal as in the above-described embodiments, for example in the manner described in WO 99/65012.

[0053] In summary, a display device has an array of pixels comprising light emitting display elements, for example EL elements, carried on a substrate and associated light sensing elements responsive to light emitted by the display elements. The light sensing elements each comprise a gated photosensitive thin film device such as a TFT structure or a lateral gated pin device having a semiconductor layer with contact regions laterally spaced on the substrate and separated by a gate controlled region. A part of the associated display element extends over the gate controlled region with an electrode of the display element serving as the gate of the photosensitive device thereby ensuring good optical coupling between the display element and the photosensitive device and enabling the gate to be appropriately biased. Such an arrangement enables, for example, the provision of electro-optic feedback control in the pixel in comparatively simple manner.

[0054] From reading the present disclosure, other modifications will be apparent to persons skilled in the art. Such

modifications may involve other features which are already known in the field of active matrix electroluminescent display devices and component parts therefor and which may be used instead of or in addition to features already described herein.

1. A light-emitting display device comprising on a substrate an array of addressable pixels each comprising a light-emitting display element having a layer of light-emitting material with a transparent electrode on one side thereof, and a light sensing element responsive to light emitted by the display element, wherein each light sensing element is a gated photosensitive thin film device comprising a semiconductor layer having contact regions laterally spaced on the substrate and an intervening gate controlled region over which dielectric material is disposed, and wherein a part of the light-emitting display element extends over the dielectric material and the gate controlled region such that the transparent electrode of the light-emitting display element at that part serves as the gate of the photosensitive device and light emitted by the light-emitting material layer is incident on the semiconductor layer.

2. A light-emitting display device according to claim 1, characterised in that the gated photosensitive device comprises a thin film transistor having laterally-spaced source and drain contact regions of doped semiconductor material and a region of intrinsic semiconductor material extending between the contact regions forming the gate controlled region.

3. A light-emitting display device according to claim 1, characterised in that the photosensitive device comprises a gated pin diode device having laterally spaced contact regions of oppositely doped type semiconductor material and a region of intrinsic semiconductor material extending between the contact regions forming the gate controlled region.

4. A light-emitting display device according to any one of claims 1 to 3, characterised in that the transparent electrode of the light-emitting element is arranged in operation of the device to be biased such that current flow in the gate controlled region is due to generated photocurrents.

5. A light-emitting display device according to claim 4, characterised in that the display element is current driven and current through the display element in a drive period is controlled by a thin film transistor based on a drive signal applied to the pixel during a preceding address period and stored as a charge on a storage capacitor coupled to the gate of the transistor, and in that the photosensitive device is coupled to the storage capacitor and acts as a charge leakage device in response to photocurrents generated therein to regulate the charge on the storage capacitor in accordance with the display element's light output.

6. A light-emitting display device according to claim 5 and claim 2, characterised in that the photosensitive device is operable as a switch and arranged to turn on in response to the potential level of the transparent electrode of the display element in the driving period reaching a threshold level to provide a conductive path between its contact regions and rapidly discharge the storage capacitor.

7. A light-emitting display device according to any one of the preceding claims, characterised in that the light-emitting material of the display elements comprises electroluminescent material.

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| 专利名称(译) | 具有光传感元件的发光矩阵阵列显示装置 | | |
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摘要(译)

一种显示装置具有像素阵列(10)，所述像素阵列包括承载在基板(50)上的发光显示元件(20)，例如EL元件，以及响应于由显示元件发射的光的相关光感测元件(40)。每个光敏元件包括门控光敏薄膜器件，例如TFT结构或具有半导体层(52)的横向栅极引脚器件，半导体层(52)具有在衬底上横向间隔开并由栅极控制区分开的接触区(53,54)。(55)。相关显示元件(20)的一部分在栅极控制区域上延伸，其中显示元件的电极(70)用作光敏器件的栅极，从而确保显示元件和光敏器件之间的良好光学耦合并使得能够实现门要适当偏见。这种布置使得例如能够以相对简单的方式在像素中提供光电反馈控制。

